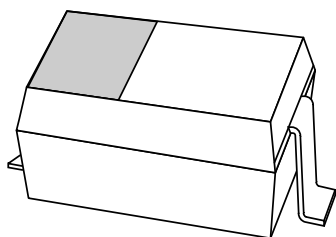


DATA SHEET



PMEG2020AEA

20 V, 2 A very low V_F MEGA
Schottky barrier rectifier in SOD323
(SC-76) package

Product data sheet

2004 Feb 26

20 V, 2 A very low V_F MEGA Schottky barrier rectifier in SOD323 (SC-76) package

PMEG2020AEA

FEATURES

- Forward current: 2 A
- Reverse voltage: 20 V
- Very low forward voltage
- Very small SMD package.

APPLICATIONS

- Low voltage rectification
- High efficiency DC/DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

MARKING

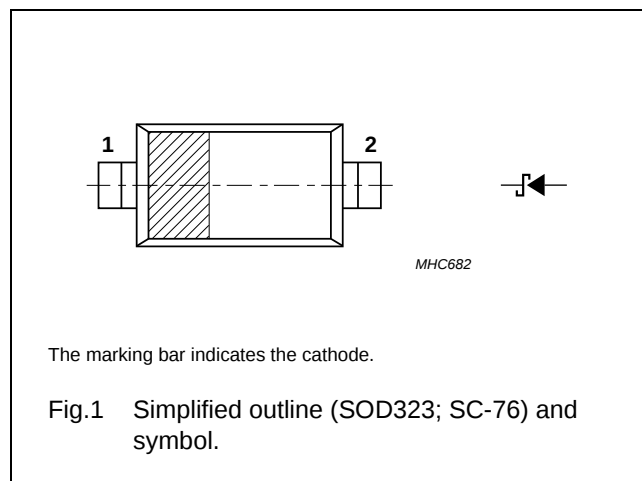
TYPE NUMBER	MARKING CODE
PMEG2020AEA	S3

QUICK REFERENCE DATA

SYMBOL	PARAMETER	VALUE	UNIT
I_F	forward current	2	A
V_R	reverse voltage	20	V

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



RELATED PRODUCTS

TYPE NUMBER	DESCRIPTION	FEATURES
PMEG1020EA	2 A; 10 V ultra low V_F MEGA Schottky barrier rectifier	SOD323 package; lower reverse voltage; lower forward voltage
PMEG2010EA	1 A; 20 V ultra low V_F MEGA Schottky barrier rectifier	SOD323 package; lower forward current; lower reverse current and diode capacitance

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMEG2020AEA	–	plastic surface mounted package; 2 leads	SOD323

20 V, 2 A very low V_F MEGA Schottky barrier rectifier in SOD323 (SC-76) package

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current	$T_{sp} \leq 55\text{ }^{\circ}\text{C}$	–	2	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}$; $\delta \leq 0.25$	–	7	A
I_{FSM}	non-repetitive peak forward current	$t = 8\text{ ms}$ square wave	–	9	A
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$
T_j	junction temperature		–	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	notes 1 and 2	450	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	notes 2 and 3	210	K/W
$R_{th(j-s)}$	thermal resistance from junction to solder point	note 4	90	K/W

Notes

1. Refer to SOD323 (SC-76) standard mounting conditions.
2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and I_F (AV) rating will be available on request.
3. Device mounted on a on an FR4 printed-circuit board with copper clad 10 x 10 mm.
4. Soldering point of cathode tab.

ELECTRICAL CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.2; note 1			
		$I_F = 0.01\text{ A}$	200	220	mV
		$I_F = 0.1\text{ A}$	265	290	mV
		$I_F = 1\text{ A}$	380	430	mV
		$I_F = 2\text{ A}$	450	525	mV
I_R	reverse current	$V_R = 5\text{ V}$; see Fig.3	15	50	μA
		$V_R = 10\text{ V}$	20	80	μA
		$V_R = 20\text{ V}$	50	200	μA
C_d	diode capacitance	$V_R = 5\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	55	70	pF

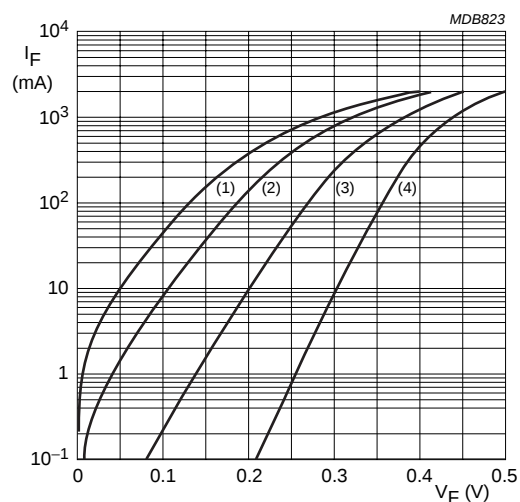
Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

20 V, 2 A very low V_F MEGA Schottky barrier rectifier in SOD323 (SC-76) package

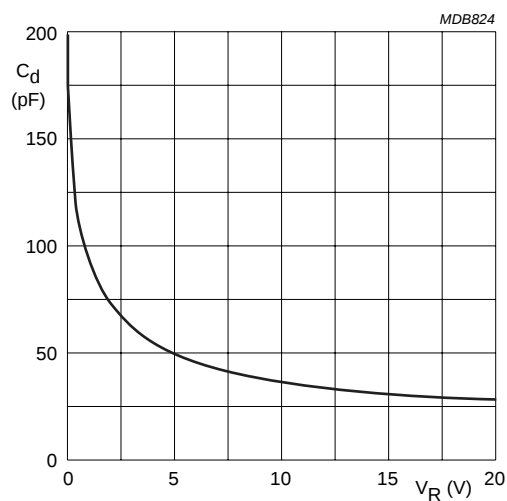
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GRAPHICAL DATA



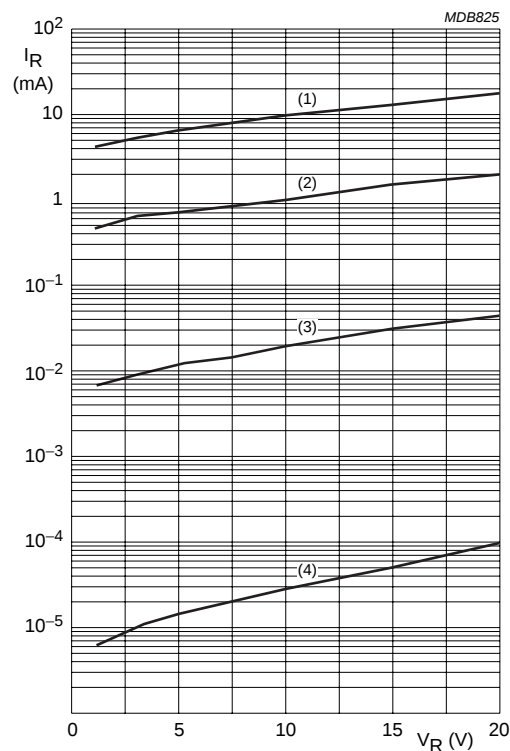
- (1) $T_{amb} = 125^\circ\text{C}$.
- (2) $T_{amb} = 85^\circ\text{C}$.
- (3) $T_{amb} = 25^\circ\text{C}$.
- (4) $T_{amb} = -40^\circ\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



$f = 1\text{ MHz}$; $T_{amb} = 25^\circ\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.



- (1) $T_{amb} = 125^\circ\text{C}$.
- (2) $T_{amb} = 85^\circ\text{C}$.
- (3) $T_{amb} = 25^\circ\text{C}$.
- (4) $T_{amb} = -40^\circ\text{C}$.

Fig.3 Reverse current as a function of reverse voltage; typical values.

20 V, 2 A very low V_F MEGA Schottky
barrier rectifier in SOD323 (SC-76) package

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PACKAGE OUTLINE

Plastic surface-mounted package; 2 leads

SOD323

DIMENSIONS (mm are the original dimensions)										
UNIT	A	A ₁ max	bp	c	D	E	HD	Lp	Q	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note
1. The marking bar indicates the cathode

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD323			SC-76			03-12-17 06-03-16

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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